

600 V, 0.1 A NPN high-voltage low VCEsat (BISS) transistor 24 June 2015 **Product data sheet**

1. **General description**

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV3160Z

2. **Features and benefits**

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability
- High collector current gain h_{FE} at high I_C •

Applications 3.

- Electronic ballast for fluorecent lighting
- LED driver for LED chain module
- LCD backlighting
- HID front lighting •
- Hook switch for wired telecom •
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	600	V
I _C	collector current		-	-	0.1	А





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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1-1
3	E	emitter		· •
4	С	collector	☐1	3 sym016

6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
PBHV2160Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Marking

Table 4. Marking codes	
Type number	Marking code
PBHV2160Z	HV216Z

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Limiting values 8.

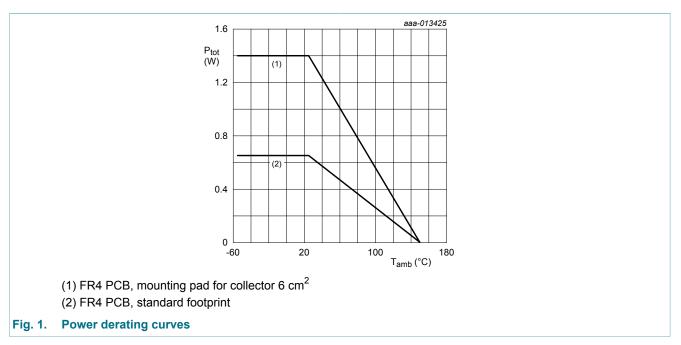
Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	600	V
V _{CEO}	collector-emitter voltage	open base		-	600	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	600	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	0.1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1.4	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [1] [2]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



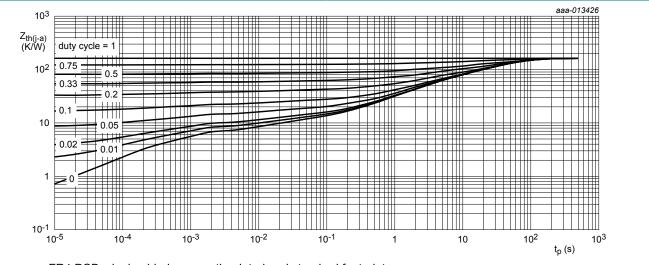
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9. Thermal characteristics

Table 6. The	ermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	190	K/W
from junction to ambient		[2]	-	-	89	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

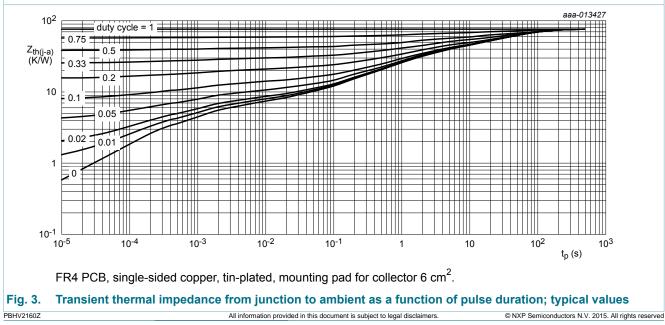
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



FR4 PCB, single-sided copper, tin-plated and standard footprint.

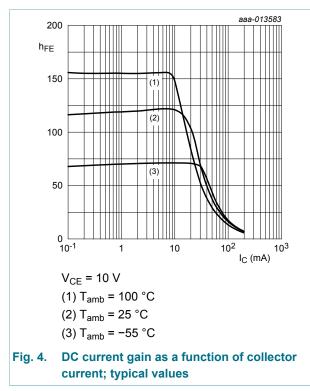


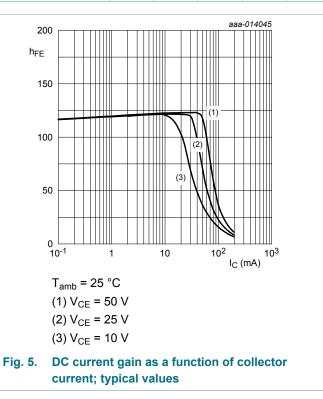


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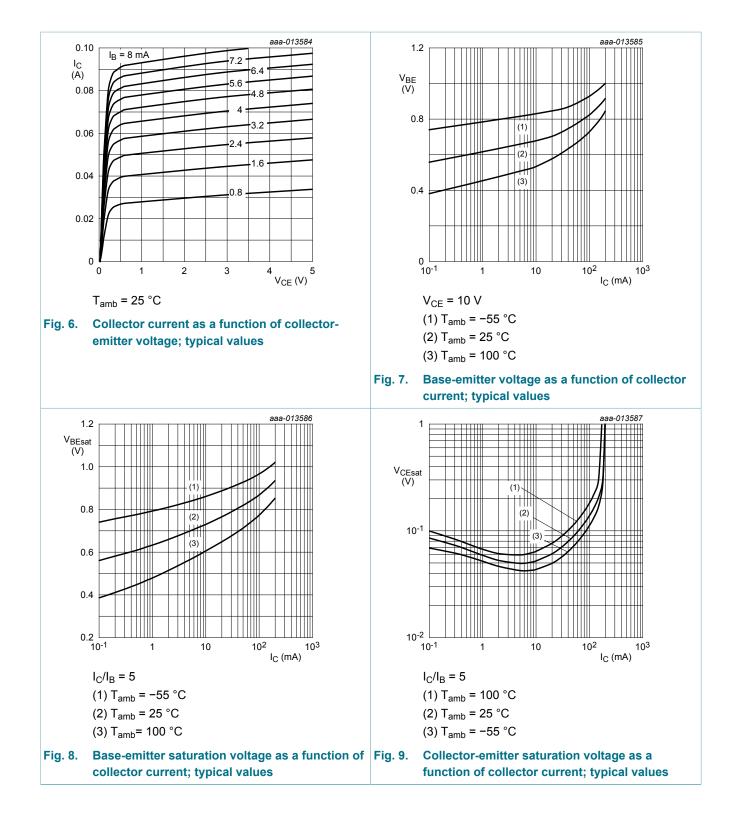
10. Characteristics

Table 7. Ch	aracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V_{CB} = 400 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 400 V; I _E = 0 A; T _j = 150 °C	-	-	10	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = 400 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = 4.8 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I _C = 10 mA; T _{amb} = 25 °C	70	125	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 30 mA; I_{B} = 6 mA; T_{amb} = 25 °C	-	65	125	mV
V _{BEsat}	base-emitter saturation voltage	I_C = 50 mA; I_B = 5 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	950	mV
C _c	collector capacitance	V _{CB} = 20 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	1.7	-	pF
C _e	emitter capacitance	V _{EB} = 0.5 V; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	81	-	pF

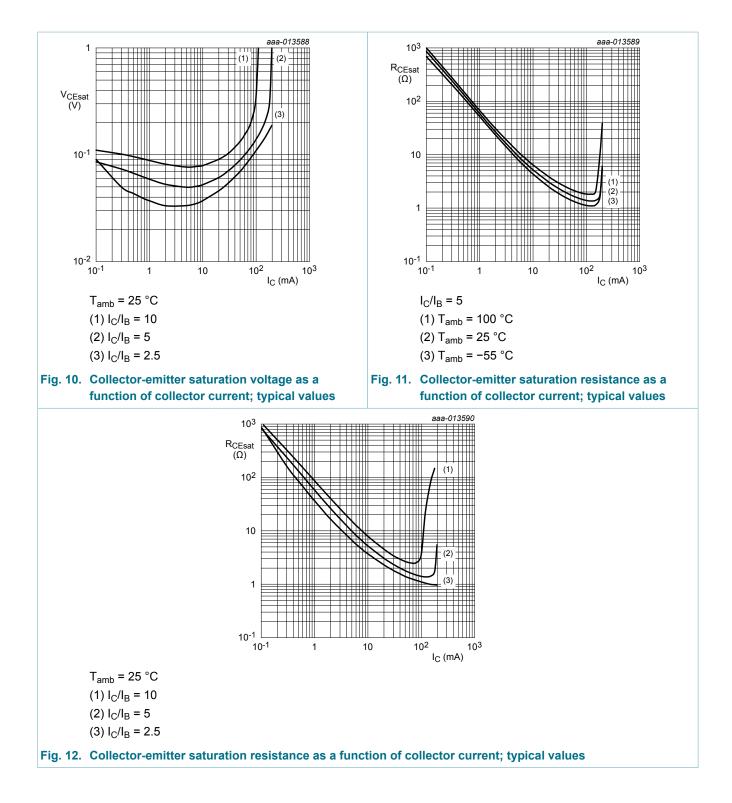




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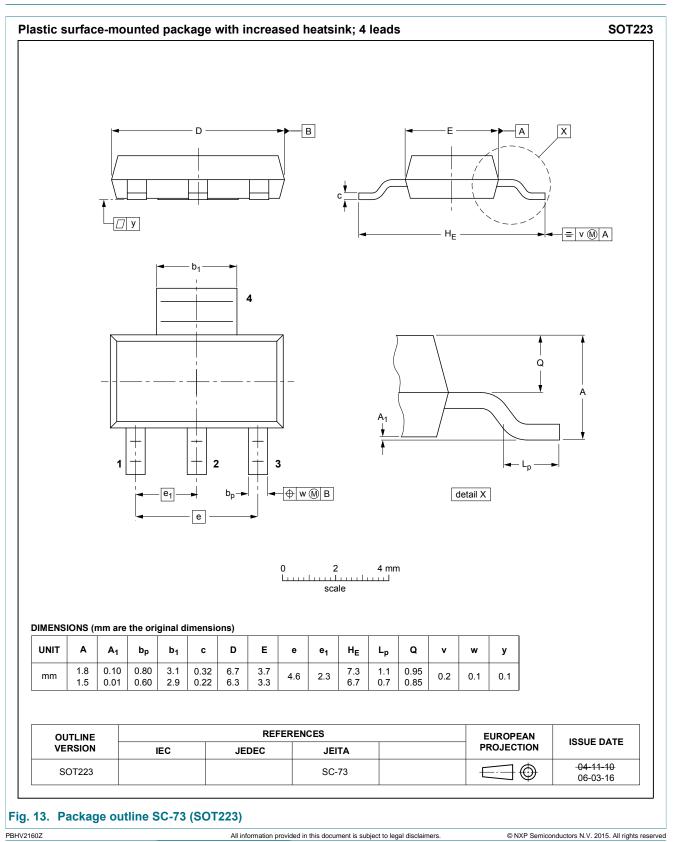


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11. Package outline

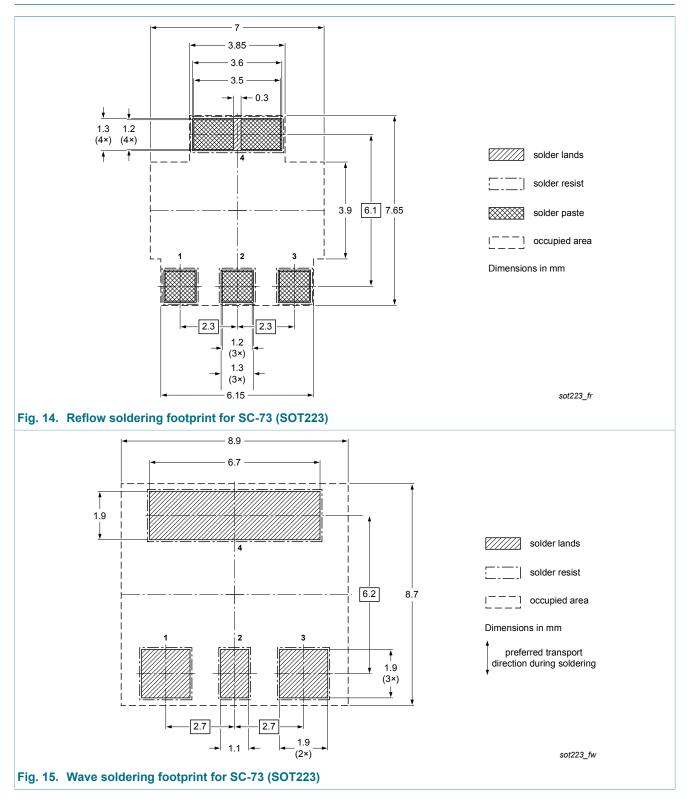


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Product data sheet

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12. Soldering



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13. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV2160Z v.1	20150624	Product data sheet	-	-

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14. Legal information

14.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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